Super-resolution enhancement method with phase-shifting mask available for random patterns

Akio Misaka, Takahiro Matsuo and Masaru Sasago
ULSI Process Technology Development Center,
Matsushita Electric industrial Co.,Ltd.
KYOTO, 601-8413, JAPAN

This paper proposes two types of phase shifting masks. One is effective for fine line patterns and the other for fine contact hole patterns. Both of them can be applied to random logic patterns without multiple exposure. Furthermore, these technologies are classified as a strong resolution enhancement technology judging from their performances. They will allow us to make sub-65-nm node logic LSIs with ArF lithography.